

Title (en)

METHOD OF ETCHING CONDUCTIVE LINES WITHOUT UNDERCUTTING

Title (de)

VERFAHREN ZUR STRUKTURIERUNG VON LEITERBAHNEN OHNE UNTERÄTZUNG

Title (fr)

PROCEDE D'ATTAQUE CHIMIQUE DES LIGNES CONDUCTRICES SANS ATTAQUE LATERALE

Publication

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Application

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Abstract (en)

[origin: WO9621243A1] Undercutting of conductive lines in a dense array bordered by an open field is avoided by reducing the severity of etching when the conductive material in the open field is substantially removed. In a preferred embodiment, the flow rate of chlorine gas is reduced during high density chlorine plasma etching of a conductive pattern when the conductive material is substantially removed from the open field.

IPC 1-7

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IPC 8 full level

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